

dielectric material which delimits the studs and keeps the studs integral with the substrate, the studs showing through on the front and rear faces of the substrate, and points of contact being formed opposite each face showing through of each stud by a conducting material insulated from the substrate.

20. (New) The substrate as claimed in claim 19, wherein the silicon studs are coated over their entire height by a conducting metallization itself surrounded by the dielectric material.

IN THE ABSTRACT

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ABSTRACT

A method of fabricating conducting through-connections in a substrate, and a substrate equipped with such connections. The method of fabricating conducting through-connections between the front face and the rear face of a substrate hollows into the substrate, from the rear-face side, cavities having a depth and a cross-section that are defined so as to delimit studs of defined cross-section, which are intended to provide for electrical conduction between the front and rear faces, and filling in the cavities with a dielectric material. The substrate is equipped with conducting through-connections between its front face and its rear face. The conducting connections are provided by way of studs delimited by cavities filled in with a dielectric material. Such a method and substrate may find application, in particular, to substrates used for the fabrication of microsensors.

REMARKS

Favorable consideration of the above-identified application, as presently amended, is respectfully requested.